

seed thin film 53, a CVD thin film 54, a PVD reflow thin film 65 sequentially formed on the barrier metal layer 52. The barrier metal layer 52 is of Ti, TiN, or Ti/TiN, wherein Ti is formed by IMP process and TiN is formed by metal-organic chemical vapor deposition (MOCVD) process. Also, the barrier metal layer 52 may be of IMP Ti or IMP Ti/TiN. The PVD seed thin film 53, the CVD thin film 54 and the PVD reflow thin film 65 are of the same material such as Al or Cu.--

Please replace the paragraph beginning on page 9, line 16 with the following:

--Meanwhile, an ARC layer 59 of Ti/TiN may further be formed on the PVD reflow thin film 55.--

Please replace the paragraph beginning on page 10, line 1 with the following:

--As shown in Fig. 6a, a barrier metal layer 62 is formed on a semiconductor substrate 61 in which an interleaving insulating film (oxide film) 67 including a contact hole 68 in a particular portion is formed. To ensure cleanness of the contact hole 68, cleaning process is performed using plasma before the barrier metal layer 62 is formed.--

Please replace the paragraph beginning on page 11, line 18 with the following:

--Additionally, to improve accuracy of a subsequent patterning process, an ARC layer 69 of Ti/TiN may be formed on the PVD reflow thin film 65.--